



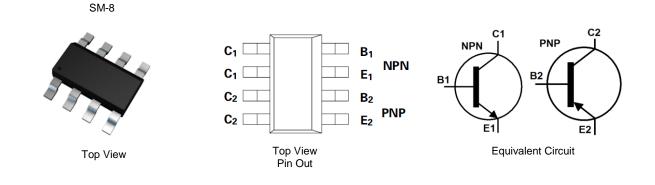
COMPLEMENTARY MEDIUM POWER HIGH GAIN TRANSISTOR IN SM-8 PACKAGE

Features

- NPN Transistor
 - BV_{CEO} > 45
 - V_{CE(sat)} < 100mV @ I_C= 100mA
 - Continuous Current I_C = 2A
- PNP Transistor
 - BV_{CEO} > -40V
 - V_{CE(sat)} < -250mV @ I_C= -500mA
 - Continuous Current I_C = -2A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.117 grams (Approximate)



Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZDT6790TA	T6790	7	12	1,000
ZDT6790TC	T6790	13	12	4,000

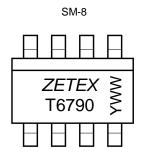
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T6790 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V _{CBO}	45	-50	V
Collector-Emitter Voltage	V _{CEO}	45	-40	V
Emitter-Base Voltage	V _{EBO}	7	-7	V
Continuous Collector Current	lc	2	-2	A
Peak Pulse Current (Note 5)	I _{CM}	6	-6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Collector Dower Discinction	(Note 5)		2.25	W
Collector Power Dissipation	(Note 6)	PD PD	2.75	vv
Thermal Desistance, Junction to Ambient	(Note 5)	P	55.60	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	45.50	- C/VV
Thermal Resistance, Junction to Leads (Note 7)		R _{θJL}	30.68	°C/W
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C

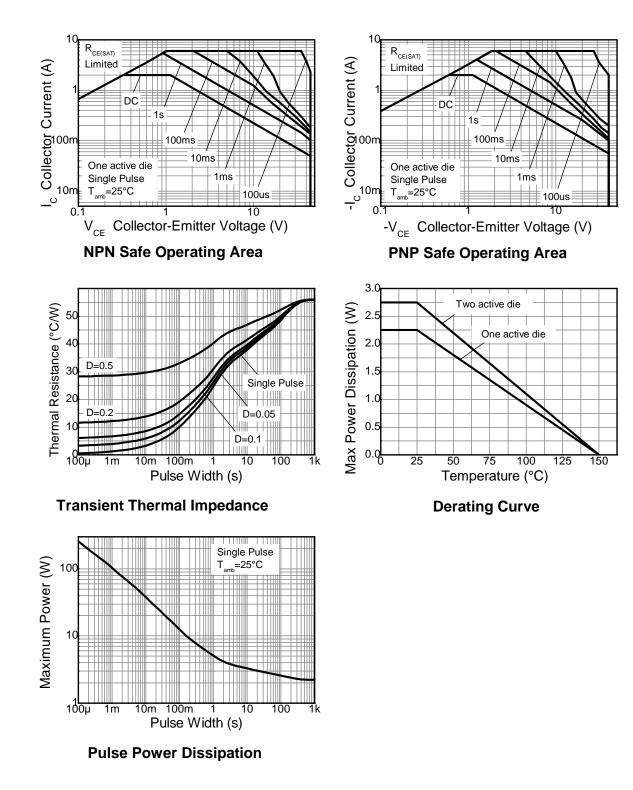
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

 For a device with any single die active and mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
Same as Note 5, except both die are active and equally sharing power.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115. Notes:



Thermal Characteristics and Derating Information





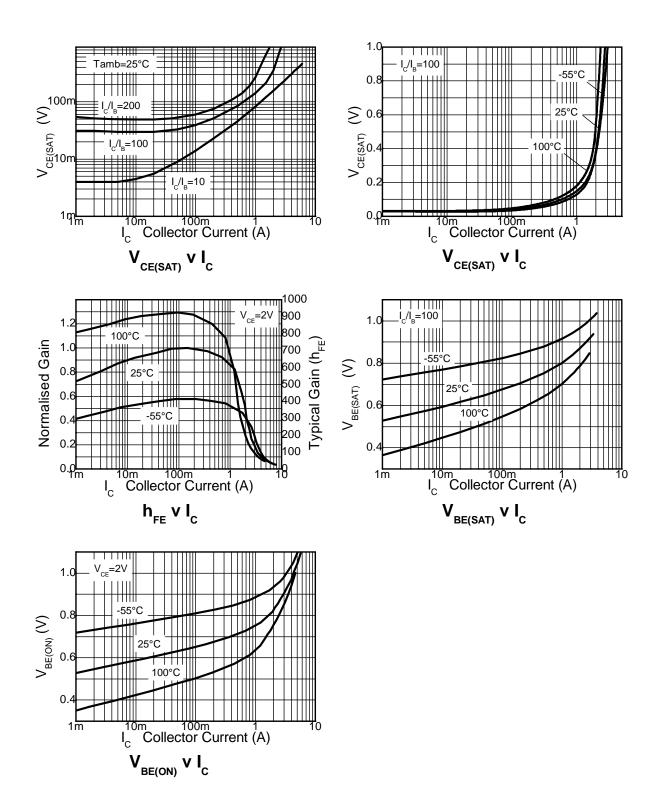
NPN - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV CBO	45	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	45	_	_	V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	—	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	—	—	100	nA	V _{CB} = 35V
Emitter Cut-Off Current	I _{EBO}	_	_	100	nA	$V_{EB} = 6V$
		500	_			$I_{C} = 100 \text{mA}, V_{CE} = 2 \text{V}$
DC Current Transfer Static Ratio (Note 9)	h _{FE}	400	_	_		$I_{C} = 1A, V_{CE} = 2V$
		150	—	—		$I_{C} = 2A, V_{CE} = 2V$
	V _{CE(sat)}	_	_	100	mV	$I_{C} = 100 \text{mA}, I_{B} = 0.5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		—	—	500		$I_{C} = 1A, I_{B} = 5mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	_	900	mV	$I_{\rm C} = 1$ A, $I_{\rm B} = 10$ mA
Base-Emitter Turn-on Voltage (Note 9)	V _{BE(on)}	_	_	900	mV	$I_{C} = 1A, V_{CE} = 2V$
Transitional Frequency (Note 9)	f _T	150	_	—	MHz	$I_C = 50$ mA, $V_{CE} = 5$ V, f = 50MHz
Input Capacitance	C _{ibo}	_	200	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	—	16		pF	V _{CB} = 10V, f = 1MHz
Switching Time	t _{on}		33		ns	$V_{CC} = 10V, I_C = 500mA,$
Switching Time	t _{off}		1,300		ns	I _{B1} = 50mA, I _{B2} = 50mA

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



NPN – Typical Electrical Characteristics





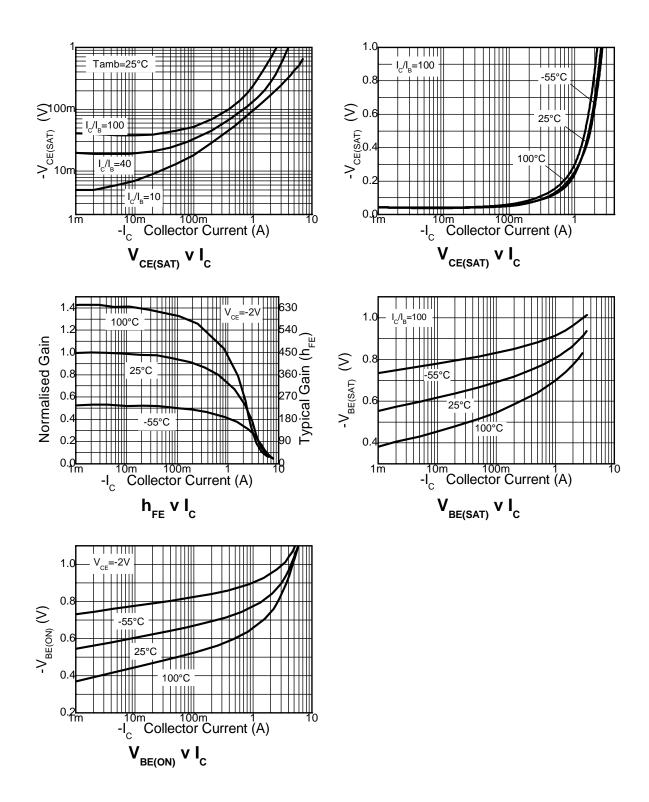
PNP - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-40	—	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}	_	—	-100	nA	V _{CB} = -30V
Emitter Cut-Off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -6V
DC Current Transfer Static Ratio (Notes 9)		300 250		800		$I_{C} = -10mA, V_{CE} = -2V$ $I_{C} = -500mA, V_{CE} = -2V$
	h _{FE}	200 150	_	_		$I_{C} = -1A, V_{CE} = -2V$ $I_{C} = -2A, V_{CE} = -2V$
Collector-Emitter Saturation Voltage (Notes 9)	V _{CE(sat)}	_		-250 -450 -750	mV	$I_{C} = -500$ mA, $I_{B} = -5$ mA $I_{C} = -1$ A, $I_{B} = -10$ mA $I_{C} = -2$ A, $I_{B} = -50$ mA
Base-Emitter Saturation Voltage (Notes 9)	V _{BE(sat)}	_	_	-1,000	mV	$I_{\rm C} = -1$ A, $I_{\rm B} = -10$ mA
Base-Emitter Turn-on Voltage (Notes 9)	V _{BE(on)}	_	-750	_	mV	I _C = -1A, V _{CE} = -2V
Transitional Frequency (Notes 9)	f⊤	100	-	—	MHz	$I_C = -50$ mA, $V_{CE} = -5V$, f = 50MHz
Input Capacitance	C _{ibo}	_	225	_	pF	V _{EB} = -0.5V, f = 1MHz,
Output Capacitance	Cobo	—	24	—	pF	$V_{CB} = -10V, f = 1MHz,$
Switching Time	t _{on}		35		ns	V _{CC} = -10V, I _C = -500mA,
	t _{off}		600		ns	$I_{B1} = -50 \text{mA}, I_{B2} = -50 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



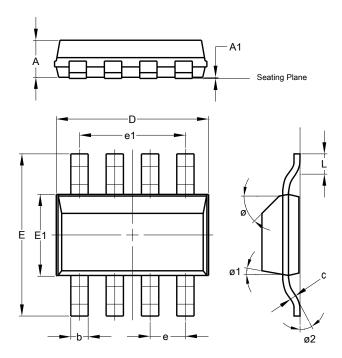
PNP – Typical Electrical Characteristics





Package Outline Dimensions

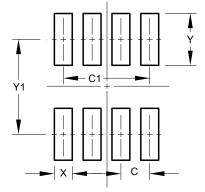
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SM-8						
Dim	Min Max Typ					
Α		1.70	1.60			
A1	0.02	0.10	0.04			
b	0.70	0.90	0.80			
c	0.24	0.32	0.28			
D	6.30	6.30 6.70 6.60				
е	1.53 REF					
e1	4.59 REF					
ш	6.70	7.30	7.00			
E1	3.30	3.70	3.50			
Г	0.75	1.00	0.90			
Ø	-	45°				
Ø1	-	15°	-			
Ø2	-	-	10°			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.52
C1	4.6
Х	0.95
Y	2.80
Y1	6.80



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